

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_c=25^\circ\text{C}$)					電気的特性 ($T_c=25^\circ\text{C}$)										外形	備考	
				V_{ce0} (V)	V_{be0} (V)	I_c (mA)	P_c (mW)	T_c ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	直流又はパルス h_{FE}		バイアス		h_{FE}	h_{ie}	h_{re}	h_{oe}	f_{α}			C_{ob}
				V_{ce} (V)	I_c (mA)	V_{ce} (V)	I_c (mA)	V_{ce} (V)	I_c (mA)	h_{FE} *	h_{ie} (Ω)	h_{re} ($\times 10^{-4}$)	h_{oe} (μS)	f_{α} (Mc)	C_{ob} (pF)	$r_{bb'}$ (Ω)					
1	2	3	4	5					6		7				8		9		10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cB0} MAXIMUM VALUE AND V_{cB} VALUE (CRITERIA FOR MEASURING I_{cB0})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{cE} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{cB} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
 - 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

